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APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.
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NIXON PEABODY, LLP 401 9TH STREET, NW SUITE 900 WASHINGTON, DC 20004-2128			EXAMINER GEBREMARIAM, SAMUEL A	
			ART UNIT 2811	PAPER NUMBER
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Please find below and/or attached an Office communication concerning this application or proceeding.

The time period for reply, if any, is set in the attached communication.

Office Action Summary

Application No.

09/578,895

Applicant(s)

YAMAZAKI ET AL.

Examiner

Samuel A. Gebremariam

Art Unit

2811

– The MAILING DATE of this communication appears on the cover sheet with the correspondence address –

Period for Reply

A SHORTENED STATUTORY PERIOD FOR REPLY IS SET TO EXPIRE 3 MONTH(S) OR THIRTY (30) DAYS, WHICHEVER IS LONGER, FROM THE MAILING DATE OF THIS COMMUNICATION.

- Extensions of time may be available under the provisions of 37 CFR 1.136(a). In no event, however, may a reply be timely filed after SIX (6) MONTHS from the mailing date of this communication.
- If NO period for reply is specified above, the maximum statutory period will apply and will expire SIX (6) MONTHS from the mailing date of this communication.
- Failure to reply within the set or extended period for reply will, by statute, cause the application to become ABANDONED (35 U.S.C. § 133). Any reply received by the Office later than three months after the mailing date of this communication, even if timely filed, may reduce any earned patent term adjustment. See 37 CFR 1.704(b).

Status

- 1) ☒ Responsive to communication(s) filed on 30 October 2007.
- 2a) ☐ This action is FINAL. 2b) ☒ This action is non-final.
- 3) ☐ Since this application is in condition for allowance except for formal matters, prosecution as to the merits is closed in accordance with the practice under *Ex parte Quayle*, 1935 C.D. 11, 453 O.G. 213.

Disposition of Claims

- 4) ☒ Claim(s) 1-10, 17-23, 25-27, 29-31, 33-36, 38, 39, 41, 42, 44-47, 49, 50, 52 and 53 is/are pending in the application.
- 4a) Of the above claim(s) 17-23 and 25-27 is/are withdrawn from consideration.
- 5) ☐ Claim(s) _____ is/are allowed.
- 6) ☒ Claim(s) 1-10, 29-31, 33-36, 38, 39, 41, 42, 44-47, 49, 50, 52 and 53 is/are rejected.
- 7) ☐ Claim(s) _____ is/are objected to.
- 8) ☐ Claim(s) _____ are subject to restriction and/or election requirement.

Application Papers

- 9) ☐ The specification is objected to by the Examiner.
- 10) ☐ The drawing(s) filed on _____ is/are: a) ☐ accepted or b) ☐ objected to by the Examiner.
Applicant may not request that any objection to the drawing(s) be held in abeyance. See 37 CFR 1.85(a).
Replacement drawing sheet(s) including the correction is required if the drawing(s) is objected to. See 37 CFR 1.121(d).
- 11) ☐ The oath or declaration is objected to by the Examiner. Note the attached Office Action or form PTO-152.

Priority under 35 U.S.C. § 119

- 12) ☐ Acknowledgment is made of a claim for foreign priority under 35 U.S.C. § 119(a)-(d) or (f).
- a) ☐ All b) ☐ Some * c) ☐ None of:
- ☐ Certified copies of the priority documents have been received.
 - ☐ Certified copies of the priority documents have been received in Application No. _____.
 - ☐ Copies of the certified copies of the priority documents have been received in this National Stage application from the International Bureau (PCT Rule 17.2(a)).

* See the attached detailed Office action for a list of the certified copies not received.

Attachment(s)

- ☒ Notice of References Cited (PTO-892)
- ☐ Notice of Draftsperson's Patent Drawing Review (PTO-948)
- ☒ Information Disclosure Statement(s) (PTO/SB/08)
Paper No(s)/Mail Date See Continuation Sheet
- ☐ Interview Summary (PTO-413)
Paper No(s)/Mail Date. _____
- ☐ Notice of Informal Patent Application
- ☐ Other: _____

Continuation of Attachment(s) 3). Information Disclosure Statement(s) (PTO/SB/08), Paper No(s)/Mail Date
:10/30/07;10/12/07;8/10/07/20/07;1/16/07.

DETAILED ACTION

Election/Restrictions

1. Applicant's election without traverse of embodiment 6 of fig. 14 in the reply filed on 10/12/07 is acknowledged.

Specification

2. The specification has not been checked to the extent necessary to determine the presence of all possible minor errors. Applicant's cooperation is requested in correcting any errors of which applicant may become aware in the specification.

Double Patenting

3. The nonstatutory double patenting rejection is based on a judicially created doctrine grounded in public policy (a policy reflected in the statute) so as to prevent the unjustified or improper timewise extension of the "right to exclude" granted by a patent and to prevent possible harassment by multiple assignees. A nonstatutory obviousness-type double patenting rejection is appropriate where the conflicting claims are not identical, but at least one examined application claim is not patentably distinct from the reference claim(s) because the examined application claim is either anticipated by, or would have been obvious over, the reference claim(s). See, e.g., *In re Berg*, 140 F.3d 1428, 46 USPQ2d 1226 (Fed. Cir. 1998); *In re Goodman*, 11 F.3d 1046, 29 USPQ2d 2010 (Fed. Cir. 1993); *In re Longi*, 759 F.2d 887, 225 USPQ 645 (Fed. Cir. 1985); *In re Van Ornum*, 686 F.2d 937, 214 USPQ 761 (CCPA 1982); *In re Vogel*, 422 F.2d 438, 164 USPQ 619 (CCPA 1970); and *In re Thorington*, 418 F.2d 528, 163 USPQ 644 (CCPA 1969).

A timely filed terminal disclaimer in compliance with 37 CFR 1.321(c) or 1.321(d) may be used to overcome an actual or provisional rejection based on a nonstatutory double patenting ground provided the conflicting application or patent either is shown to be commonly owned with this application, or claims an invention made as a result of activities undertaken within the scope of a joint research agreement.

Effective January 1, 1994, a registered attorney or agent of record may sign a terminal disclaimer. A terminal disclaimer signed by the assignee must fully comply with 37 CFR 3.73(b).

4. Claims 1, 5, 33 and 44 are provisionally rejected on the ground of nonstatutory obviousness-type double patenting as being unpatentable over claims 1-14 of copending Application No. 10/980,603 (603).

This is a provisional obviousness-type double patenting rejection because the conflicting claims have not in fact been patented.

Regarding claim 1, (603) teaches (claim 1) an electroluminescence display device comprising: a substrate (the EL device is inherently formed on a substrate); a plurality of pixels over the substrate, each of the plurality of pixels comprising: a first thin film transistor; a second thin film transistor comprising a gate electrode electrically connected to the first thin film transistor (603, teaches a switching TFT and current-control TFT and both inherently have a gate electrode); and an electroluminescence element electrically connected to the second thin film transistor, wherein the first thin film transistor comprises at least two channel regions in an active layer (switching transistor has two TFTs and hence two channel regions), at least two gate electrodes corresponding to the channel regions, over the active layer with a gate insulating film interposed therebetween, and an impurity region interposed between the channel regions (TFTs inherently have source and drain region, hence impurity regions).

Regarding claim 5, (603) teaches the entire claimed structure of claim 1 above including the first thin film transistor is a switching thin film transistor and the second thin film transistor is a current control thin film transistor (refer to claim 1).

Regarding claim 33, (603) teaches (claim 1) an electroluminescence display device comprising: a substrate; and a plurality of pixels over the substrate, each of the

plurality of pixels comprising: a switching element comprising an active layer and at least first and second gate electrodes (two TFTs inherently have two gate electrodes) adjacent to the active layer with a gate insulating film interposed therebetween; a current control element comprising a gate electrode electrically connected to the switching element; and an electroluminescence element electrically connected to the current control element (refer to claim 1).

Regarding claim 44, (603) teaches (claim 1) an electroluminescence display device comprising: a substrate; and a plurality of pixels over the substrate, each of the plurality of pixels comprising: a switching element comprising at least two thin film transistors; a current control element comprising a gate electrode electrically connected to the switching element; and an electroluminescence element electrically connected to the current control element.

5. Claims 1, 5, 8, 33, 35 and 44 are provisionally rejected on the ground of nonstatutory obviousness-type double patenting as being unpatentable over claims 1-18 of copending Application No.10/337,391 (391).

Regarding claim 1, (391) teaches (claim 1) an electroluminescence display device comprising: a substrate (the EL device is inherently formed on a substrate); a plurality of pixels over the substrate, each of the plurality of pixels comprising: a first thin film transistor; a second thin film transistor comprising a gate electrode electrically connected to the first thin film transistor (603, teaches a switching TFT and current-control TFT and both inherently have a gate electrode); and an electroluminescence

element electrically connected to the second thin film transistor, wherein the first thin film transistor comprises at least two channel regions in an active layer (switching transistor has two TFTs and hence two channel regions), at least two gate electrodes corresponding to the channel regions, over the active layer with a gate insulating film interposed therebetween, and an impurity region interposed between the channel regions (LDD regions).

Regarding claim 5, (391) teaches the entire claimed structure of claim 1 above including the first thin film transistor is a switching thin film transistor and the second thin film transistor is a current control thin film transistor (refer to claim 1).

Regarding claim 8, (391) teaches the entire claimed structure of claim 1 above including wherein each of the first and second thin film transistors has at least one lightly doped impurity region between a channel region and one of a drain region or the impurity regions where the lightly doped impurity region of the first thin film transistor does not overlap a gate electrode of the first thin film transistor and the lightly doped impurity region of the second thin film transistor overlaps a gate electrode of the second thin film transistor at least partly (refer to claim 1).

Regarding claim 29, (391) teaches (claim 1) an electroluminescence display device comprising: a substrate; and a plurality of pixels over the substrate, each of the plurality of pixels comprising: a first thin film transistor; a second thin film transistor comprising a gate electrode electrically connected to the first thin film transistor; and an electroluminescence element electrically connected to the second thin film transistor, wherein the first thin film transistor comprises an active layer in which at least two

channel regions connected in series are formed with an impurity region interposed therebetween, and wherein each of the first and second thin film transistors has at least one lightly doped impurity region between a channel region and one of a impurity regions where the lightly doped impurity region of the first thin film transistor does not overlap a gate electrode of the first thin film transistor and the lightly doped impurity region of the second thin film transistor overlaps a gate electrode of the second thin film transistor at least partly.

Regarding claim 30, (391) teaches substantially the entire claimed structure of claims 2 and 3 above including the first thin film transistor is a switching thin film transistor and the second thin film transistor is a current control thin film transistor (claim 1).

Regarding claims 33 and 35, (391) teaches (claim 1) an electroluminescence display device comprising: a substrate; and a plurality of pixels over the substrate, each of the plurality of pixels comprising: a switching element comprising an active layer and at least first and second gate electrodes (two TFTs inherently have two gate electrodes) adjacent to the active layer with a gate insulating film interposed therebetween; a current control element comprising a gate electrode electrically connected to the switching element; and an electroluminescence element electrically connected to the current control element (refer to claim 1).

Regarding claim 41, (391) teaches (claim 1) an electroluminescence display device comprising: a substrate; and a plurality of pixels over the substrate, each of the plurality of pixels comprising: a switching element comprising an active layer and at

least first and second gate electrodes adjacent to a the active layer with a gate insulating film interposed therebetween; a current control element comprising a gate electrode electrically connected to the switching element; and an electroluminescence element electrically connected to the current control element, wherein each of the switching element and the current control element has at least one lightly doped impurity region where, wherein the lightly doped impurity region of the switching element does not overlap a gate electrode of the switching element and the lightly doped impurity region of the current control element overlaps a gate electrode of the current control element at least partly.

Regarding claims 44, 46 and 52, (391) teaches (claim 1) the entire claimed structure of claim 41 above including an electroluminescence display device comprising: a substrate; and a plurality of pixels over the substrate, each of the plurality of pixels comprising: a switching element comprising at least two thin film transistors; a current control element comprising a gate electrode electrically connected to the switching element; and an electroluminescence element electrically connected to the current control element.

6. Claims 1-10, 29-31, 33-36, 38-39, 41-42, 44-47, 49-50, 52-53 are provisionally rejected on the ground of nonstatutory obviousness-type double patenting as being unpatentable over claims 17-30 of copending Application No.11/258,933 (933).

Regarding claims 1-10, 29-30, 33-35, 38, 41-42, 44-46, 49 and 52 (933) teaches (claims 1-10) an electroluminescence display device comprising: a substrate (the EL

device is inherently formed on a substrate); a plurality of pixels over the substrate, each of the plurality of pixels comprising: a first thin film transistor; a second thin film transistor comprising a gate electrode electrically connected to the first thin film transistor; and an electroluminescence element electrically connected to the second thin film transistor, wherein the first thin film transistor comprises at least two channel regions in an active layer (switching transistor has two TFTs and hence two channel regions), at least two gate electrodes corresponding to the channel regions, over the active layer with a gate insulating film interposed therebetween, and an impurity region interposed between the channel regions (LDD regions). Furthermore (933) teaches that a channel width of the second thin film transistor is greater than a channel width of the first thin film transistor or wherein an equation of $W2/L2 > 5 \times W1/L1$ establishes where a channel length of the second thin film transistor is $L2$ (0.1-50 μ m), a channel width of the second thin film transistor is $W2$ (0.5 to 30 μ m), a channel length of the first thin film transistor is $L1$ (0.2 to 18 μ m) and a channel width of the first thin film transistor is $W1$ (0.1 to 5 μ m) (claim 3). In addition (933) teaches (claims 5-10) a current control element comprising a gate electrode electrically connected to the switching element; and an electroluminescence element electrically connected to the current control element, wherein each of the switching element and the current control element has at least one lightly doped impurity region where, wherein the lightly doped impurity region of the switching element does not overlap a gate electrode of the switching element and the lightly doped impurity region of the current control element overlaps a gate electrode of the current control element at least partly. Furthermore it would have been obvious to

one of ordinary skill in the art at the time the invention was made to form a plurality of pixels in the structure of (933), in order to form a functional display device. Furthermore (933) teaches substantially the entire claimed structure of claims 29, 33, 41, 44, 49 and 52 above including the substrate comprises a material selected from the group consisting of a glass, a glass ceramic, a quartz, a silicon, a ceramic, a metal, and a plastic (refer to claim 22 and 29).

7. Claims 2-4, 34, 38-39, 45, 49 and 50 are provisionally rejected on the ground of nonstatutory obviousness-type double patenting as being unpatentable over claims 1-18 of copending Application No. 10/980,603 (603) in view of Luo, US patent No., 4,040,073.

Regarding claims 2, 3-4, 9-10, 34, 38, 45 and 49 (603) teaches substantially the entire claimed structure of claim 1 except explicitly stating that a channel width of the second thin film transistor is greater than a channel width of the first thin film transistor or wherein an equation of $W2/L2 > 5 \times W1/L1$ establishes where a channel length of the second thin film transistor is $L2$ (0.1-50 μ m), a channel width of the second thin film transistor is $W2$ (0.5 to 30 μ m), a channel length of the first thin film transistor is $L1$ (0.2 to 18 μ m) and a channel width of the first thin film transistor is $W1$ (0.1 to 5 μ m).

Luo teaches a switching thin film transistor T1 and a current control TFT T2, where the channel width can be adjusted depending on the function of the device (col. 3, lines 45-55).

It would have been obvious to one of ordinary skill in the art at the time the invention was made to adjust a channel width of the second thin film transistor and a channel width of the first thin film transistor as claimed as taught by Luo in the structure of (603) in order to form a device with improved stability (col. 2, lines 16-25).

Furthermore parameters such as channel length and channel width in the art of semiconductor manufacturing are subject to routine experimentation and optimization to achieve the desired device characteristics during fabrication.

Therefore, it would have been obvious to one of ordinary skill in the art at the time the invention was made to adjust the channel length and channel width as claimed in the structure of (603) in order to form a device with improved stability (col. 2, lines 16-25).

Regarding claims 6 and 7, (603) teaches substantially the entire claimed structure of claims 2 and 3 above including the first thin film transistor is a switching thin film transistor and the second thin film transistor is a current control thin film transistor (claim 1).

Regarding claims 39 and 50, (603) teaches substantially the entire claimed structure of claims 2-3, 38 and 49 above including the substrate is glass (12, fig. 1, Luo).

8. Claims 2-4, 31, 34, 36, 38-39, 42, 45, 47, 49, 50 and 53 are provisionally rejected on the ground of nonstatutory obviousness-type double patenting as being unpatentable

over claims 1-18 of copending Application No. 10/337,391 (391) in view of Luo, US patent No., 4,040,073.

Regarding claims 2, 3-4, 9-10, 34, 38, 45 and 49 (391) teaches substantially the entire claimed structure of claims 1 except explicitly stating that a channel width of the second thin film transistor is greater than a channel width of the first thin film transistor or wherein an equation of $W2/L2 > 5 \times W1/L1$ establishes where a channel length of the second thin film transistor is $L2$ (0.1-50 μ m), a channel width of the second thin film transistor is $W2$ (0.5 to 30 μ m), a channel length of the first thin film transistor is $L1$ (0.2 to 18 μ m) and a channel width of the first thin film transistor is $W1$ (0.1 to 5 μ m).

Luo teaches a switching thin film transistor T1 and a current control TFT T2, where the channel width can be adjusted depending on the function of the device (col. 3, lines 45-55).

It would have been obvious to one of ordinary skill in the art at the time the invention was made to adjust a channel width of the second thin film transistor and a channel width of the first thin film transistor as claimed as taught by Luo in the structure of (391) in order to form a device with improved stability (col. 2, lines 16-25).

Furthermore parameters such as channel length and channel width in the art of semiconductor manufacturing are subject to routine experimentation and optimization to achieve the desired device characteristics during fabrication.

Therefore, it would have been obvious to one of ordinary skill in the art at the time the invention was made to adjust the channel length and channel width as claimed

in the structure of (391) in order to form a device with improved stability (col. 2, lines 16-25).

Regarding claims 6 and 7, (391) teaches substantially the entire claimed structure of claims 2 and 3 above including the first thin film transistor is a switching thin film transistor and the second thin film transistor is a current control thin film transistor (claim 1).

Regarding claims 9 and 10, (391) teaches substantially the entire claimed structure of claims 2 and 3 above including wherein each of the first and second thin film transistors has at least one lightly doped impurity region between a channel region and one of a drain region or the impurity regions wherein the lightly doped impurity region of the first thin film transistor does not overlap a gate electrode of the first thin film transistor and the lightly doped impurity region of the second thin film transistor overlaps a gate electrode of the second thin film transistor at least partly (refer to claim 1).

Regarding claims 31, 36, 42, 47, 50 and 53, (391) teaches substantially the entire claimed structure of claims 29, 33, 41, 44, 49 and 52 above except explicitly stating that the wherein the substrate comprises a material selected from the group consisting of a glass, a glass ceramic, a quartz, a silicon, a ceramic, a metal, and a plastic.

Luo teaches an electroluminescence device that is based on a glass substrate (12) in order to form a device with improved stability.

It would have been obvious to one of ordinary skill in the art at the time the invention was made to form the electroluminescence device of (391) on a glass substrate as taught by Luo in order to form a device with improved stability.

Claim Rejections - 35 USC § 102

9. The following is a quotation of the appropriate paragraphs of 35 U.S.C. 102 that form the basis for the rejections under this section made in this Office action:

A person shall be entitled to a patent unless –

(e) the invention was described in a patent granted on an application for patent by another filed in the United States before the invention thereof by the applicant for patent, or on an international application by another who has fulfilled the requirements of paragraphs (1), (2), and (4) of section 371(c) of this title before the invention thereof by the applicant for patent.

10. Claims 1, 5, 33 and 44 are rejected under 35 U.S.C. 102(e) as being anticipated by Sasaki et al., US patent No. 5,790,213.

Regarding claim 1, Sasaki teaches (figs. 1-6) an electroluminescence display device comprising: a substrate (col. 8, lines 52-53); a plurality of pixels (col. 8, lines 37-42) over the substrate, each of the plurality of pixels comprising: a first thin film transistor (5, 6); a second thin film transistor (7a, 7b) comprising a gate electrode electrically connected to the first thin film transistor (refer to fig. 2); and an electroluminescence element (col. 8, lines 43-46) electrically connected to the second thin film transistor (fig. 2), wherein the first thin film transistor comprises at least two channel regions in an active layer (5, 6 two transistors hence two channel regions), at least two gate electrodes (two transistors hence two gate electrodes) corresponding to the channel regions, over the active layer with a gate insulating film interposed

therebetween, and an impurity region interposed between the channel regions (inherent structural characteristics of a transistor structure).

Regarding claim 5, Sasaki teaches the entire claimed structure of claim 1 above including the first thin film transistor (5, 6) is a switching thin film transistor and the second thin film (7) transistor is a current control thin film transistor (refer to claim 2).

Regarding claim 33, Sasaki teaches (figs. 1-6) an electroluminescence display device comprising: a substrate (col. 8, lines 52-53); and a plurality of pixels (col. 8, lines 37-42) over the substrate, each of the plurality of pixels comprising: a switching element (5, 6) comprising an active layer and at least first and second gate electrodes (two TFTs inherently have two gate electrodes) adjacent to the active layer with a gate insulating film interposed therebetween; a current control element (7) comprising a gate electrode electrically connected to the switching element (refer to fig. 2); and an electroluminescence element (col. 8, lines 43-46) electrically connected to the current control element (refer to fig. 2).

Regarding claim 44, Sasaki teaches (figs. 1-6) an electroluminescence display device comprising: a substrate (col. 8, lines 52-53); and a plurality of pixels (col. 8, lines 37-42) over the substrate, each of the plurality of pixels comprising: a switching element (5,6) comprising at least two thin film transistors; a current control element (7) comprising a gate electrode electrically connected to the switching element (fig. 2); and an electroluminescence element (col. 8, lines 43-46) electrically connected to the current control element.

Claim Rejections - 35 USC § 103

11. The following is a quotation of 35 U.S.C. 103(a) which forms the basis for all obviousness rejections set forth in this Office action:

(a) A patent may not be obtained though the invention is not identically disclosed or described as set forth in section 102 of this title, if the differences between the subject matter sought to be patented and the prior art are such that the subject matter as a whole would have been obvious at the time the invention was made to a person having ordinary skill in the art to which said subject matter pertains. Patentability shall not be negated by the manner in which the invention was made.

12. Claims 2, 3-4, 6-7, 34, 38, 45 and 49 are rejected under 35 U.S.C. 103(a) as being unpatentable over Sasaki in view Luo.

Regarding claims 2, 3-4, 6-7, 34, 38, 45 and 49 Sasaki teaches substantially the entire claimed structure of claims 1 and 5 except explicitly stating that a channel width of the second thin film transistor is greater than a channel width of the first thin film transistor or wherein an equation of $W2/L2 > 5 \times W1/L1$ establishes where a channel length of the second thin film transistor is $L2$ (0.1-50 μ m), a channel width of the second thin film transistor is $W2$ (0.5 to 30 μ m), a channel length of the first thin film transistor is $L1$ (0.2 to 18 μ m) and a channel width of the first thin film transistor is $W1$ (0.1 to 5 μ m).

Luo teaches a switching thin film transistor T1 and a current control TFT T2, where the channel width can be adjusted depending on the function of the device (col. 3, lines 45-55).

It would have been obvious to one of ordinary skill in the art at the time the invention was made to adjust a channel width of the second thin film transistor and a channel width of the first thin film transistor as claimed as taught by Luo in the structure of Sasaki in order to form a device with improved stability (col. 2, lines 16-25).

Furthermore parameters such as channel length and channel width in the art of semiconductor manufacturing are subject to routine experimentation and optimization to achieve the desired device characteristics during fabrication.

Therefore, it would have been obvious to one of ordinary skill in the art at the time the invention was made to adjust the channel length and channel width as claimed in the structure of Sasaki in order to form a device with improved stability (col. 2, lines 16-25).

Regarding claims 8-10, 35, 41, 46 and 52 Sasaki teaches substantially the entire claimed structure of claims 1-3, 33 and 44 above including each of the first and second thin film transistors has at least one lightly doped impurity region between a channel region and one of a drain region or the impurity regions wherein the lightly doped impurity region of the first thin film transistor does not overlap a gate electrode of the first thin film transistor and the lightly doped impurity region of the second thin film transistor overlaps a gate electrode of the second thin film transistor at least partly (refer to fig. 2).

Regarding claims 29-30, Sasaki teaches substantially the entire claimed structure of claims 1-3 and 8-10 including the first thin film transistor is a switching thin film transistor (5, 6) and the second thin film transistor (7) is a current control thin film transistor (Sasaki, fig. 2).

Regarding claims 31, 36, 42, 47, 50 and 53, Sasaki teaches substantially the entire claimed structure of claims 29, 33, 41, 44, 49 and 52 above including the substrate is glass (col. 2, line 46).

Conclusion

Any inquiry concerning this communication or earlier communications from the examiner should be directed to Samuel A Gebremariam whose telephone number is (571) 272-1653. The examiner can normally be reached on 8:00am-4:30pm.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Lynne Gurley can be reached on (571) 272-1670. The fax phone number for the organization where this application or proceeding is assigned is 703-872-9306.

Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR or Public PAIR. Status information for unpublished applications is available through Private PAIR only. For more information about the PAIR system, see <http://pair-direct.uspto.gov>. Should you have questions on access to the Private PAIR system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free).

SAG
December 7, 2007

Samuel Admassu Gebremariam

